

Xuerui Niu

List of Publications by Year in descending order

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6
papers

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1937685

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6
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21
citing authors

#	ARTICLE	IF	CITATIONS
1	AlN/GaN/InGaN Coupling-Channel HEMTs for Improved <i>g_m</i> and Gain Linearity. IEEE Transactions on Electron Devices, 2021, 68, 3308-3313.	3.0	24
2	The DC Performance and RF Characteristics of GaN-Based HEMTs Improvement Using Graded AlGaIn Back Barrier and Fe/C Co-Doped Buffer. IEEE Transactions on Electron Devices, 2022, 69, 4170-4174.	3.0	13
3	Improved RF Power Performance of AlGaIn/GaN HEMT Using by Ti/Au/Al/Ni/Au Shallow Trench Etching Ohmic Contact. IEEE Transactions on Electron Devices, 2021, 68, 4842-4846.	3.0	8
4	Electrical Degradation of <i>In Situ</i> SiN/AlGaIn/GaN MIS-HEMTs Caused by Dehydrogenation and Trap Effect Under Hot Carrier Stress. IEEE Transactions on Electron Devices, 2021, 68, 4283-4288.	3.0	5
5	Investigation on the Influence of Ohmic Structure on Channel-to-Channel Coupling Effect in InAlN/GaN Double Channel HEMTs. IEEE Journal of the Electron Devices Society, 2022, 10, 474-480.	2.1	4
6	Analytical Model on the Threshold Voltage of p-Channel Heterostructure Field-Effect Transistors on a GaN-Based Complementary Circuit Platform. IEEE Transactions on Electron Devices, 2022, 69, 57-62.	3.0	3